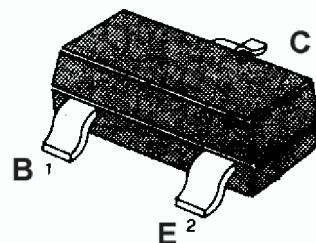


APPLICATION: High Voltage Amplifier Applications.

MAXIMUM RATINGS (Ta=25°C)

| PARAMETER | SYMBOL | RATING | UNIT |
|-----------------------------|------------------|---------|------|
| Collector-base voltage | V _{CBO} | 450 | V |
| Collector-emitter voltage | V _{CEO} | 400 | V |
| Emitter-base voltage | V _{EBO} | 6 | V |
| Collector current | I _C | 300 | mA |
| Collector Power Dissipation | P _C | 350 | mW |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature Range | T _{stg} | -55~150 | °C |

SOT-23



1.Base 2.Emitter 3.Collector

ELECTRICAL CHARACTERISTICS (Ta=25°C)

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNIT | TEST CONDITION |
|--------------------------------------|----------------------|------|------|------|------|---|
| DC Current Gain | h _{FE1} | 45 | | 200 | | V _{CE} = 10V, I _C = 10mA |
| | h _{FE2} | 20 | | | | V _{CE} = 10V, I _C = 100mA |
| Collector Cut-off Current | I _{CBO} | | | 0.1 | μ A | V _{CB} = 400V, I _E =0 |
| Emitter Cut-off Current | I _{EBO} | | | 0.1 | μ A | V _{EB} = 4V, I _C =0 |
| Collector-Base Breakdown Voltage | BV _{CBO} | 450 | | | V | I _C = 0.1mA, I _E =0 |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | 400 | | | V | I _C = 1mA, I _B =0 |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 6 | | | V | I _E = 0.01mA, I _C =0 |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | | | 0.5 | V | I _C = 10mA, I _B = 1mA |
| | V _{CE(sat)} | | | 0.75 | V | I _C = 50mA, I _B = 5mA |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | | | 0.75 | V | I _C = 10mA, I _B =1 mA |
| Gain bandwidth product | f _T | 50 | | | MHz | I _C =10mA, V _{CE} =10V, f=10MHz |
| Common Base Output Capacitance | C _{ob} | | | 7 | pF | V _{CB} = 20V, I _E =0, f= 1MHz |

h_{FE} Classification and Marking

Print Mark

Classification

h_{FE} 45~200